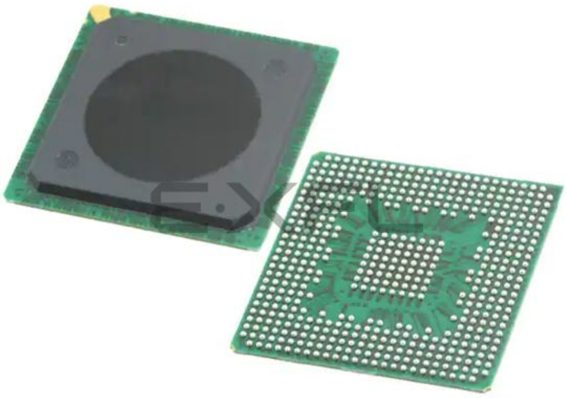

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8323eczqafdc

1 Overview

The MPC8323E incorporates the e300c2 (MPC603e-based) core built on Power Architecture® technology, which includes 16 Kbytes of L1 instruction and data caches, dual integer units, and on-chip memory management units (MMUs). The e300c2 core does not contain a floating point unit (FPU). The MPC8323E also includes a 32-bit PCI controller, four DMA channels, a security engine, and a 32-bit DDR1/DDR2 memory controller.

A new communications complex based on QUICC Engine technology forms the heart of the networking capability of the MPC8323E. The QUICC Engine block contains several peripheral controllers and a 32-bit RISC controller. Protocol support is provided by the main workhorses of the device—the unified communication controllers (UCCs). Note that the MPC8321 and MPC8321E do not support UTOPIA. A block diagram of the MPC8323E is shown in Figure 1.

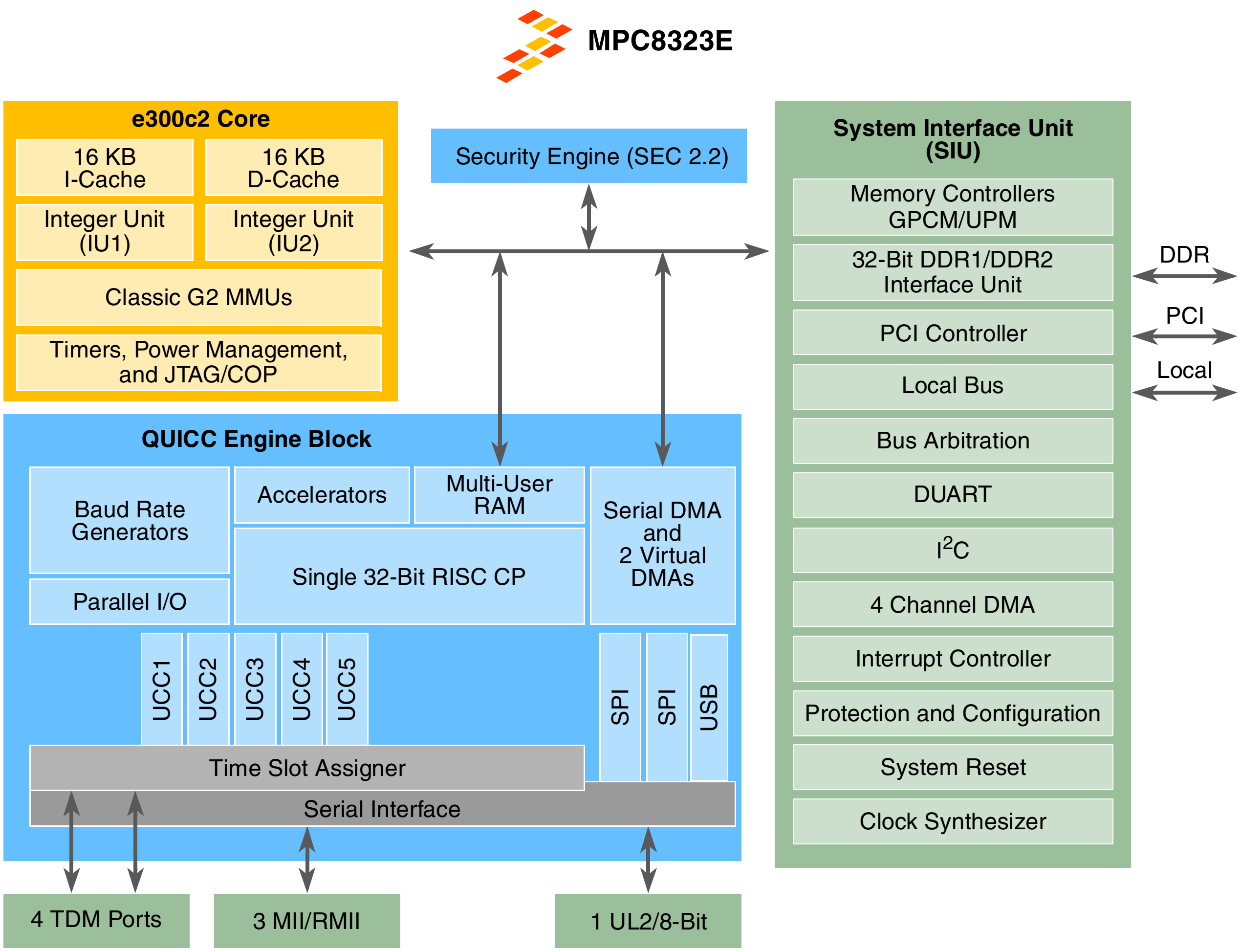


Figure 1. MPC8323E Block Diagram

Each of the five UCCs can support a variety of communication protocols: 10/100 Mbps Ethernet, serial ATM, HDLC, UART, and BISYNC—and, in the MPC8323E and MPC8323, multi-PHY ATM and ATM support for up to OC-3 speeds.

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8323E. The MPC8323E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage		AV_{DDn}	–0.3 to 1.26	V	—
DDR1 and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
PCI, local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.6	V	—
Input voltage	DDR1/DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2
	DDR1/DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2
	Local bus, DUART, CLKIN, system control and power management, I^2C, SPI, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	5
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV_{DD} = 3.3 V
PCI signals	25	
DDR1 signal	18	GV_{DD} = 2.5 V
DDR2 signal	18	GV_{DD} = 1.8 V
DUART, system control, I2C, SPI, JTAG	42	OV_{DD} = 3.3 V
GPIO signals	42	OV_{DD} = 3.3 V

2.1.4 Input Capacitance Specification

Table 4 describes the input capacitance for the CLKIN pin in the MPC8323E.

Table 4. Input Capacitance Specification

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input capacitance for all pins except CLKIN	C_I	6	8	pF	—
Input capacitance for CLKIN	C_{ICLKIN}	10	—	pF	1

Note:
1. The external clock generator should be able to drive 10 pF.

2.2 Power Sequencing

The device does not require the core supply voltage (V_{DD}) and IO supply voltages (GV_{DD} and OV_{DD}) to be applied in any particular order. Note that during power ramp-up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3. Once both the power supplies (I/O voltage and core voltage) are stable, wait for a minimum of 32 clock cycles before negating $\overline{\text{PORESET}}$.

Note that there is no specific power down sequence requirement for the device. I/O voltage supplies (GV_{DD} and OV_{DD}) do not have any ordering requirements with respect to one another.

Table 11. Reset Signals DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	±5	μA	—

Note:
1. This specification applies when operating from 3.3 V supply.

6 DDR1 and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR1 and DDR2 SDRAM interface of the MPC8323E. Note that DDR1 SDRAM is Dn_GV_{DD}(typ) = 2.5 V and DDR2 SDRAM is Dn_GV_{DD}(typ) = 1.8 V. The AC electrical specifications are the same for DDR1 and DDR2 SDRAM.

6.1 DDR1 and DDR2 SDRAM DC Electrical Characteristics

Table 12 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8323E when Dn_GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM DC Electrical Characteristics for Dn_GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	Dn_GV_{DD}	1.71	1.89	V	1
I/O reference voltage	$MVREFn_{REF}$	$0.49 \times Dn\_GV_{DD}$	$0.51 \times Dn\_GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MVREFn_{REF} - 0.04$	$MVREFn_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MVREFn_{REF} + 0.125$	$Dn\_GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MVREFn_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	–9.9	9.9	μA	4
Output high current (V_{OUT} = 1.35 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. Dn_GV_{DD} is expected to be within 50 mV of the DRAM Dn_GV_{DD} at all times.
2. $MVREFn_{REF}$ is expected to be equal to $0.5 \times Dn\_GV_{DD}$, and to track Dn_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MVREFn_{REF}$ may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to $MVREFn_{REF}$. This rail should track variations in the DC level of $MVREFn_{REF}$.
4. Output leakage is measured with all outputs disabled, $0 \text{ V} \leq V_{OUT} \leq Dn\_GV_{DD}$.

Table 13 provides the DDR2 capacitance when Dn_GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for Dn_GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1

Table 13. DDR2 SDRAM Capacitance for Dn_GV$_{DD}$(typ) = 1.8 V

Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. Dn_GV$_{DD}$ = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25 °C, V_{OUT} = Dn_GV$_{DD}$ ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR1 SDRAM component(s) of the MPC8323E when Dn_GV$_{DD}$(typ) = 2.5 V.

Table 14. DDR1 SDRAM DC Electrical Characteristics for Dn_GV$_{DD}$(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	Dn_GV$_{DD}$	2.375	2.625	V	1
I/O reference voltage	MVREFn_{REF}	0.49 × Dn_GV$_{DD}$	0.51 × Dn_GV$_{DD}$	V	2
I/O termination voltage	V_{TT}	MVREFn_{REF} – 0.04	MVREFn_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MVREFn_{REF} + 0.15	Dn_GV$_{DD}$ + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MVREFn_{REF} – 0.15	V	—
Output leakage current	I_{OZ}	–9.9	–9.9	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. Dn_GV$_{DD}$ is expected to be within 50 mV of the DRAM Dn_GV$_{DD}$ at all times.
2. MVREFn_{REF} is expected to be equal to 0.5 × Dn_GV$_{DD}$, and to track Dn_GV$_{DD}$ DC variations as measured at the receiver. Peak-to-peak noise on MVREFn_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREFn_{REF}. This rail should track variations in the DC level of MVREFn_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ Dn_GV$_{DD}$.

Table 15 provides the DDR1 capacitance Dn_GV$_{DD}$(typ) = 2.5 V.

Table 15. DDR1 SDRAM Capacitance for Dn_GV$_{DD}$(typ) = 2.5 V Interface

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ,DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. Dn_GV$_{DD}$ = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = Dn_GV$_{DD}$ ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 24. MII Receive AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
RX_CLK clock fall time	t_{MRXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 8 provides the AC test load.

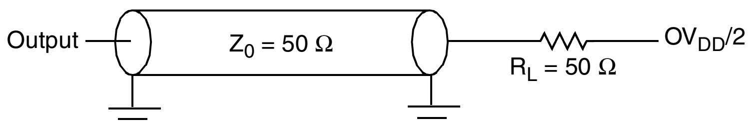


Figure 8. AC Test Load

Figure 9 shows the MII receive AC timing diagram.

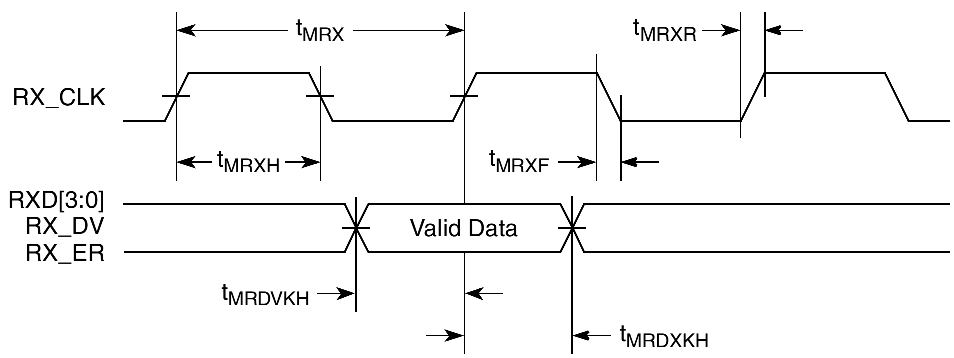


Figure 9. MII Receive AC Timing Diagram

8.2.2 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

Table 32. JTAG AC Timing Specifications (Independent of CLKIN)[1] (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol[2]	Min	Max	Unit	Notes
JTAG external clock to output high impedance:				ns	
Boundary-scan data	t_{JTKLDZ}	2	19		5, 6
TDO	t_{JTKLOZ}	2	9		6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 14). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.
6. Guaranteed by design and characterization.

Figure 18 provides the AC test load for TDO and the boundary-scan outputs of the MPC8323E.

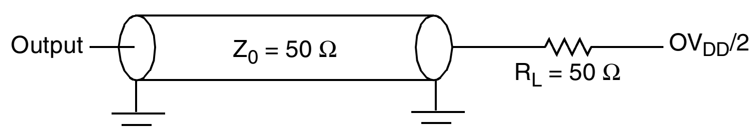


Figure 18. AC Test Load for the JTAG Interface

Figure 19 provides the JTAG clock input timing diagram.

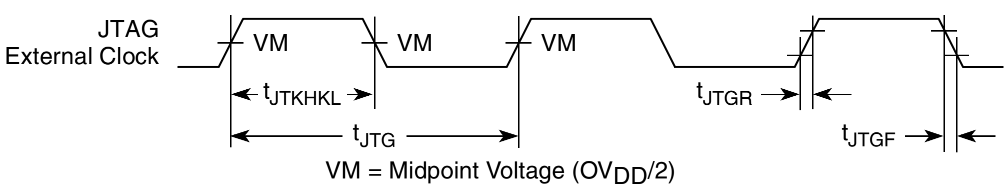


Figure 19. JTAG Clock Input Timing Diagram

Figure 20 provides the $\overline{\text{TRST}}$ timing diagram.

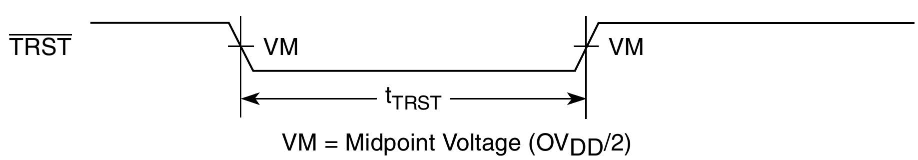


Figure 20. $\overline{\text{TRST}}$ Timing Diagram

Figure 28 provides the AC test load for the timers.

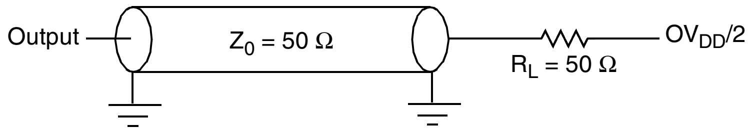


Figure 28. Timers AC Test Load

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the MPC8323E.

14.1 GPIO DC Electrical Characteristics

Table 11 provides the DC electrical characteristics for the MPC8323E GPIO.

Table 40. GPIO DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	1
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±5	μA	—

Note:
1. This specification applies when operating from 3.3-V supply.

14.2 GPIO AC Timing Specifications

Table 41 provides the GPIO input and output AC timing specifications.

Table 41. GPIO Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

Figure 29 provides the AC test load for the GPIO.

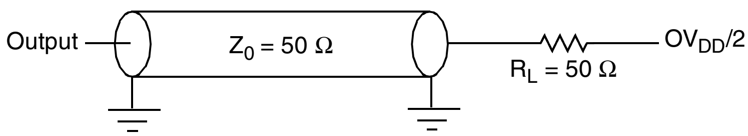


Figure 29. GPIO AC Test Load

15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8323E.

15.1 IPIC DC Electrical Characteristics

Table 42 provides the DC electrical characteristics for the external interrupt pins of the MPC8323E.

Table 42. IPIC DC Electrical Characteristics[1,2]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, $\overline{\text{MCP\_OUT}}$, and CE ports Interrupts.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

15.2 IPIC AC Timing Specifications

Table 43 provides the IPIC input and output AC timing specifications.

Table 43. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

19 HDLC, BISYNC, Transparent, and Synchronous UART

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), BISYNC, transparent, and synchronous UART of the MPC8323E.

19.1 HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Table 50 provides the DC electrical characteristics for the MPC8323E HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 50. HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -2.0$ mA	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 3.2$ mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \leq V_{IN} \leq OV_{DD}$	—	±5	μA

19.2 HDLC, BISYNC, Transparent, and Synchronous UART AC Timing Specifications

Table 51 provides the input and output AC timing specifications for HDLC, BISYNC, and transparent UART protocols.

Table 51. HDLC, BISYNC, and Transparent UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	t_{HIKHOV}	0	5.5	ns
Outputs—External clock delay	t_{HEKHOV}	1	10	ns
Outputs—Internal clock high impedance	t_{HIKHOX}	0	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	6	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	0	—	ns

Table 51. HDLC, BISYNC, and Transparent UART AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit
Inputs—External clock input hold time	t_{HEIXKH}	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{HIKHOX} symbolizes the outputs internal timing (HI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Table 52. Synchronous UART AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	5.5	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	10	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	5.5	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	8	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	4	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	0	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, $t_{UAIKHOX}$ symbolizes the outputs internal timing (UAI) for the time t_{serial} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 38 provides the AC test load.

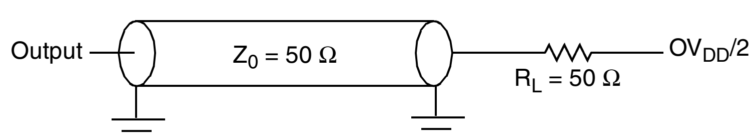


Figure 38. AC Test Load

Figure 39 and Figure 40 represent the AC timing from Table 51. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8323E.

20.1 USB DC Electrical Characteristics

Table 53 provides the DC electrical characteristics for the USB interface.

Table 53. USB DC Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±5	µA

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

20.2 USB AC Electrical Specifications

Table 54 describes the general timing parameters of the USB interface of the MPC8323E.

Table 54. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at OV_{DD}/2 of the rising or falling edge of the signals.

Figure 41 provide the AC test load for the USB.

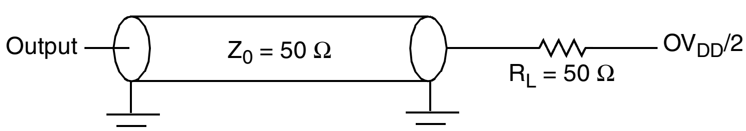


Figure 41. USB AC Test Load

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MDQ29	AD20	IO	GV_{DD}	—
MEMC_MDQ30	AF23	IO	GV_{DD}	—
MEMC_MDQ31	AD22	IO	GV_{DD}	—
MEMC_MDM0	AC9	O	GV_{DD}	—
MEMC_MDM1	AD5	O	GV_{DD}	—
MEMC_MDM2	AE20	O	GV_{DD}	—
MEMC_MDM3	AE22	O	GV_{DD}	—
MEMC_MDQS0	AE8	IO	GV_{DD}	—
MEMC_MDQS1	AE5	IO	GV_{DD}	—
MEMC_MDQS2	AC19	IO	GV_{DD}	—
MEMC_MDQS3	AE23	IO	GV_{DD}	—
MEMC_MBA0	AD16	O	GV_{DD}	—
MEMC_MBA1	AD17	O	GV_{DD}	—
MEMC_MBA2	AE17	O	GV_{DD}	—
MEMC_MA0	AD12	O	GV_{DD}	—
MEMC_MA1	AE12	O	GV_{DD}	—
MEMC_MA2	AF12	O	GV_{DD}	—
MEMC_MA3	AC13	O	GV_{DD}	—
MEMC_MA4	AD13	O	GV_{DD}	—
MEMC_MA5	AE13	O	GV_{DD}	—
MEMC_MA6	AF13	O	GV_{DD}	—
MEMC_MA7	AC15	O	GV_{DD}	—
MEMC_MA8	AD15	O	GV_{DD}	—
MEMC_MA9	AE15	O	GV_{DD}	—
MEMC_MA10	AF15	O	GV_{DD}	—
MEMC_MA11	AE16	O	GV_{DD}	—
MEMC_MA12	AF16	O	GV_{DD}	—
MEMC_MA13	AB16	O	GV_{DD}	—
$\overline{\text{MEMC\_MWE}}$	AC17	O	GV_{DD}	—
$\overline{\text{MEMC\_MRAS}}$	AE11	O	GV_{DD}	—
$\overline{\text{MEMC\_MCAS}}$	AD11	O	GV_{DD}	—
$\overline{\text{MEMC\_MCS}}$	AC11	O	GV_{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LCS1	AB25	O	OV_{DD}	4
LCS2	AA23	O	OV_{DD}	4
LCS3	AA24	O	OV_{DD}	4
LWE0	Y23	O	OV_{DD}	4
LWE1	W25	O	OV_{DD}	4
LBCTL	V25	O	OV_{DD}	4
LALE	V24	O	OV_{DD}	7
CFG_RESET_SOURCE[0]/LSDA10/LGPL0	L23	IO	OV_{DD}	—
CFG_RESET_SOURCE[1]/LSDWE/LGPL1	K23	IO	OV_{DD}	—
LSDRAS/LGPL2/LOE	J23	O	OV_{DD}	4
CFG_RESET_SOURCE[2]/LSDCAS/LGPL3	H23	IO	OV_{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	G23	IO	OV_{DD}	4, 8
LGPL5	AC22	O	OV_{DD}	4
LCLK0	Y24	O	OV_{DD}	7
LCLK1	Y25	O	OV_{DD}	7
DUART				
UART_SOUT1/MSRCID0 (DDR ID)/LSRCID0	G1	IO	OV_{DD}	—
UART_SIN1/MSRCID1 (DDR ID)/LSRCID1	G2	IO	OV_{DD}	—
UART_CTS1/MSRCID2 (DDR ID)/LSRCID2	H3	IO	OV_{DD}	—
UART_RTS1/MSRCID3 (DDR ID)/LSRCID3	K3	IO	OV_{DD}	—
UART_SOUT2/MSRCID4 (DDR ID)/LSRCID4	H2	IO	OV_{DD}	—
UART_SIN2/MDVAL (DDR ID)/LDVAL	H1	IO	OV_{DD}	—
UART_CTS2	J3	IO	OV_{DD}	—
UART_RTS2	K4	IO	OV_{DD}	—
I^2C interface				
IIC_SDA/CKSTOP_OUT	AE24	IO	OV_{DD}	2
IIC_SCL/CKSTOP_IN	AF24	IO	OV_{DD}	2
Programmable Interrupt Controller				
MCP_OUT	AD25	O	OV_{DD}	—
IRQ0/MCP_IN	AD26	I	OV_{DD}	—
IRQ1	K1	IO	OV_{DD}	—
IRQ2	K2	I	OV_{DD}	—

The *ce_clk* frequency is determined by the QUICC Engine PLL multiplication factor (RCWL[CEPMF) and the QUICC Engine PLL division factor (RCWL[CEPDF]) according to the following equation:

When CLKIN is the primary input clock,

$$ce\_clk = (\text{primary clock input} \times \text{CEPMF}) \div (1 + \text{CEPDF})$$

When PCI_CLK is the primary input clock,

$$ce\_clk = [\text{primary clock input} \times \text{CEPMF} \times (1 + \sim\text{CFG\_CLKIN\_DIV})] \div (1 + \text{CEPDF})$$

See the “QUICC Engine PLL Multiplication Factor” section and the “QUICC Engine PLL Division Factor” section in the *MPC8323E PowerQUICC II Pro Communications Processor Reference Manual* for more information.

The DDR SDRAM memory controller operates with a frequency equal to twice the frequency of *csb_clk*. Note that *ddr_clk* is not the external memory bus frequency; *ddr_clk* passes through the DDR clock divider (÷2) to create the differential DDR memory bus clock outputs (MCK and $\overline{\text{MCK}}$). However, the data rate is the same frequency as *ddr_clk*.

The local bus memory controller operates with a frequency equal to the frequency of *csb_clk*. Note that *lbc_clk* is not the external local bus frequency; *lbc_clk* passes through the LBC clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBC clock divider ratio is controlled by LCRR[CLKDIV]. See the “LBC Bus Clock and Clock Ratios” section in the *MPC8323E PowerQUICC II Pro Communications Processor Reference Manual* for more information.

In addition, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. These units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset. Table 56 specifies which units have a configurable clock frequency. Refer to the “System Clock Control Register (SCCR)” section in the *MPC8323E PowerQUICC II Pro Communications Processor Reference Manual* for a detailed description.

Table 56. Configurable Clock Units

Unit	Default Frequency	Options
Security core, I2C, SAP, TPR	*csb_clk*	Off, *csb_clk*/2, *csb_clk*/3
PCI and DMA complex	*csb_clk*	Off, *csb_clk*

NOTE

Setting the clock ratio of these units must be performed prior to any access to them.

Table 57 provides the operating frequencies for the 8323E PBGA under recommended operating conditions (see Table 2).

Table 57. Operating Frequencies for PBGA

Characteristic[1]	Max Operating Frequency	Unit
e300 core frequency (*core_clk*)	333	MHz
Coherent system bus frequency (*csb_clk*)	133	MHz
QUICC Engine frequency (*ce_clk*)	200	MHz

Table 57. Operating Frequencies for PBGA (continued)

Characteristic[1]	Max Operating Frequency	Unit
DDR1/DDR2 memory bus frequency (MCLK)[2]	133	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz
PCI input frequency (CLKIN or PCI_CLK)	66	MHz

[1] The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.
[2] The DDR1/DDR2 data rate is 2× the DDR1/DDR2 memory bus frequency.
[3] The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBCM]).

22.4 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 58 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO divider).

The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 300–600 MHz.

Table 58. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

As described in Section 22, “Clocking,” the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the $\overline{\text{CFG\_CLKIN\_DIV}}$ configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 59

22.7 Suggested PLL Configurations

To simplify the PLL configurations, the MPC8323E might be separated into two clock domains. The first domain contain the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the csb_clk as its input clock. The second clock domain has the QUICC Engine PLL. The clock domains are independent, and each of their PLLs are configured separately. Both of the domains has one common input clock. Table 63 shows suggested PLL configurations for 33, 25, and 66 MHz input clocks.

Table 63. Suggested PLL Configurations

Conf No.	SPMF	Core PLL	CEMF	CEDF	Input Clock Frequency (MHz)	CSB Frequency (MHz)	Core Frequency (MHz)	QUICC Engine Frequency (MHz)
1	0100	0000100	0110	0	33.33	133.33	266.66	200
2	0100	0000101	1000	0	25	100	250	200
3	0010	0000100	0011	0	66.67	133.33	266.66	200
4	0100	0000101	0110	0	33.33	133.33	333.33	200
5	0101	0000101	1000	0	25	125	312.5	200
6	0010	0000101	0011	0	66.67	133.33	333.33	200

23 Thermal

This section describes the thermal specifications of the MPC8323E.

23.1 Thermal Characteristics

Table 64 provides the package thermal characteristics for the 516 27 × 27 mm PBGA of the MPC8323E.

Table 64. Package Thermal Characteristics for PBGA

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	$R_{\theta JA}$	28	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	$R_{\theta JA}$	21	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	$R_{\theta JMA}$	23	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	$R_{\theta JMA}$	18	°C/W	1, 3
Junction-to-board	—	$R_{\theta JB}$	13	°C/W	4
Junction-to-case	—	$R_{\theta JC}$	9	°C/W	5

interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8323E.

24.1 System Clocking

The MPC8323E includes three PLLs.

- The system PLL ($AV_{DD}2$) generates the system clock from the externally supplied CLKIN input. The frequency ratio between the system and CLKIN is selected using the system PLL ratio configuration bits as described in Section 22.4, "System PLL Configuration."
- The e300 core PLL ($AV_{DD}3$) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in Section 22.5, "Core PLL Configuration."
- The QUICC Engine PLL ($AV_{DD}1$) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.

24.2 PLL Power Supply Filtering

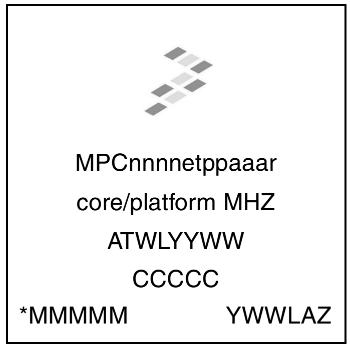
Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each $AV_{DD}n$ pin should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in Figure 44, one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

25.2 Part Marking

Parts are marked as in the example shown in Figure 46.



PBGA

Notes:
ATWLYYWW is the traceability code.
CCCCC is the country code.
MMMMM is the mask number.
YWWLAZ is the assembly traceability code.

Figure 46. Freescale Part Marking for PBGA Devices

26 Document Revision History

Table 67 provides a revision history for this hardware specification.

Table 67. Document Revision History

Rev. No.	Date	Substantive Change(s)
4	09/2010	• Replaced all instances of “LCCR” with “LCRR” throughout. • Added footnotes 3 and 4 in Table 2, “Recommended Operating Conditions[3].” • Modified Section 8.1.1, “DC Electrical Characteristics.” • Modified Table 23, “MII Transmit AC Timing Specifications.” • Modified Table 24, “MII Receive AC Timing Specifications.” • Added footnote 7 and 8, and modified some signal names in Table 55, ”MPC8323E PBGA Pinout Listing.”
3	12/2009	• Removed references for note 4 from Table 1. • Added Figure 2 in Section 2.1.2, “Power Supply Voltage Specification. • Added symbol T_A in Table 2. • Added footnote 2 in Table 2. • Added a note in Section 4, “Clock Input Timing for rise/fall time of QE input pins. • Modified CLKIN, PCI_CLK rise/fall time parameters in Table 8. Modified min value of t_{MCK} in Table 19. • Modified Figure 43. • Modified formula for ce_clk calculation in Section 22.3, “System Clock Domains. • Added a note in Section 22.4, “System PLL Configuration. • Removed the signal ECID_TMODE_IN from Table 55. • Removed all references of RST signals from Table 55.

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Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku
Tokyo 153-0064
Japan
0120 191014 or
+81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor China Ltd.
Exchange Building 23F
No. 118 Jianguo Road
Chaoyang District
Beijing 100022
China
+86 10 5879 8000
support.asia@freescale.com

For Literature Requests Only:
Freescale Semiconductor
Literature Distribution Center
1-800 441-2447 or
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Fax: +1-303-675-2150
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